

Title	Home institution	Host Institution
Investigating and engineering surface band bending of MBE-grown semiconducting oxide layers as a tool to tailor electronic contact properties	University College London (UK)	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)
Transmission Electron Microscopy (TEM) study of dislocation filtering layers and strain in epitaxial III-Vs on Silicon	Institut d'Electronique et des Systèmes (France)	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)
Development of Scalable Quantum Triple Hybrid Materials	Niels Bohr Institute, University of Copenhagen (Denmark)	Institute of Physics of the Czech Academy of Sciences, Department of Spintronics and Nanoelectronics (Czech Republic)
Towards in-operando HAXPES of ferroelectric AlScN-based capacitors	Universität Konstanz (Germany)	Institute of Materials Science of Barcelona, ICMAB-CSIC (Spain)
Sunlight driven photocatalytic dye degradation using GaN nanowires	National Institute for R&D in Microtechnologies (Romania)	Center for Nanosciences and Nanotechnology, CNRS, Paris-Saclay University (France)
Model system electrocatalysts for operando characterisation at oxygen evolution reaction potentials	University of Twente (The Netherlands)	Technical University of Denmark (Denmark)
Magnetron Sputter Epitaxy of GaN and AlN for Electronic Device Application	Fraunhofer FEP (Germany)	IFM at Linköping University (Sweden)
Thickness dependency on electrical mobility of free-standing NSTO membranes	Technical University of Denmark (Denmark)	Leibniz Institut für Kristallzüchtung (Germany)
Top-down fabrication of nanowires containing a GaN-based p-n junction for advanced microscopy studies	Commissariat à l'Energie Atomique et aux Energies Alternatives, CEA (France)	Institute of High-Pressure Physics (IHPP) of the Polish Academy of Sciences (Poland)
Characterisation of thin-film lithium-garnet electrolyte using in-situ/operando Multi-wavelength Ellipsometry/Raman spectroscopy	Technical University of Denmark (Denmark)	Catalonia Institute for Energy Research, IREC (Spain)
Investigating the Oxidation/Reduction Mechanism of Zinc Phosphide by In-Situ Transmission Electron Microscopy	Institut Catala de Nanociencia i Nanotecnologia, ICN2 (Spain)	NanoLund Centre for Nanoscience, LUND University (Sweden)
Investigating the carrier dynamics in GaAsSb/GaAsN short-period superlattices using time-resolved cathodoluminescence	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)	University of Cambridge, Department of Materials Science and Metallurgy (UK)
Strain-engineering of free-standing oxide thin films	Leibniz Institut für Kristallzüchtung (Germany)	Technical University Denmark (Denmark)
Time-resolved cathodoluminescence study of carrier diffusion in Ga(As,Sb) nanowires	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)	University of Cambridge (UK)
The growth of dislocation filter layers for the epitaxy of III-Sb on Si for in-situ microscopy investigations	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)	Institut d'Electronique et des Systèmes, Université de Montpellier (France)

Advanced Epitaxial Control in III-V Nanowires for Quantum Dot Fabrication	DTU Nanolab - Technical University of Denmark (Denmark)	C2N – Université Paris-Saclay (France)
Surface and interface characterization of anatase (001) TiO ₂ ultrathin films grown by MBE on STO and LAO (001) substrates	Institute of Materials Science of Barcelona, ICMA-B-CSIC (Spain)	Institut Néel, CNRS (France)
Fundamental understanding of interface sharpness in Ge-QWL heterostructures	Leibniz Institut für Kristallzüchtung (Germany)	Polytechnique Montreal (Canada)
Germanium Passivation by Thin-Film GaAs Layers Grown Using Low-Temperature Epitaxial Plasma Deposition	Instituto de Energía Solar – Universidad Politécnica de Madrid (Spain)	LPICM, CNRS, Ecole Polytechnique, Institut Polytechnique de Paris (France)
Pushing the limits of μ SOFCs – from freestanding thin films to single repeating units.	IREC - Fundación Instituto de Investigación de la Energía de Cataluña (Spain)	Technische Hochschule Deggendorf (Germany)
Manufacturing and Investigation of Epitaxial Layer based on Boron-Doped GaSe Thin Film	Baku State University (Azerbaijan)	Electrical and Computer Engineering Department, University of the Peloponnese (Greece)
High-resolution (scanning) transmission electron microscopy of novel piezoelectric (Al,Sc)N nanowires	Paul-Drude-Institute for Solid State Electronics, Leibniz Institut im Forschungsverbund Berlin e.V. (Germany)	Centre de Recherche sur l'Hétéroépitaxie et ses Applications, CRHEA (France)
Epitaxial Growth and Characterization of Graphene over SiC	University of Valencia (Spain)	University of York (UK)
Epitaxial spin valve structures of functional La–Ba–Mn–Ti–O manganite for memory applications*	ISSAT-MAHDIA, University of Monastir (Tunisia)	National Institute of Materials Physics (Romania)

(*) After being granted, this STSM was cancelled by grantee due to logistic reasons.